



Power MOSFETS

DATASHEET

LM1F098NHV2A

N-Channel
Enhancement Mode MOSFET

 Leadpower-semiconductor Corp., Ltd

 sales@leadpower-semi.com

 (03) 6577339 FAX : (03) 6577229

 www.leadpower-semi.com

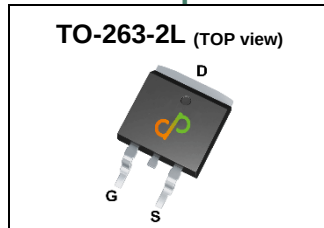


Quality Management Systems

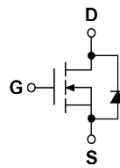
ISO 9001:2015 Certificate

N-Channel Enhancement Mode MOSFET

Pin Description



Symbol



Product Summary

Symbol	N-Channel	Unit
V_{DS}	150	V
$R_{DS(ON)-Max}$	10	m Ω
ID	149	A

Feature

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS and Rg Tested

Applications

- Synchronous Rectification in SMPS
- Hard Switching and High Speed Circuit
- DC/DC in Telecoms and Industrial

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM1F098NHV2A	TO-263-2L	Tape & Reel	800 / Tape & Reel	1F098 □□□□□□

Note : □□□□□□ = Lot Code

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
V_{DS}	Drain-Source Voltage	150	V
V_{GS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$	207
$I_{DM}^{(1)}$	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$	373
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$	149
		$T_C=100^\circ\text{C}$	91
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$	227
		$T_C=100^\circ\text{C}$	91
I_D	Continuous Drain Current	$T_A=25^\circ\text{C}$	14
		$T_A=70^\circ\text{C}$	11
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$	2.0
		$T_A=70^\circ\text{C}$	1.3
$I_{AS}^{(2)}$	Avalanche Current, Single pulse	$L=0.1\text{mH}$	42
$E_{AS}^{(2)}$	Avalanche Energy, Single pulse	$L=0.1\text{mH}$	88

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	0.55
$R_{\theta JA}^{(3)}$	Thermal Resistance-Junction to Ambient	Steady State	62

Note ① : Max. current is limited by junction temperature

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C

Note ③ : Surface Mounted on 1in^2 FR-4 board with 1oz

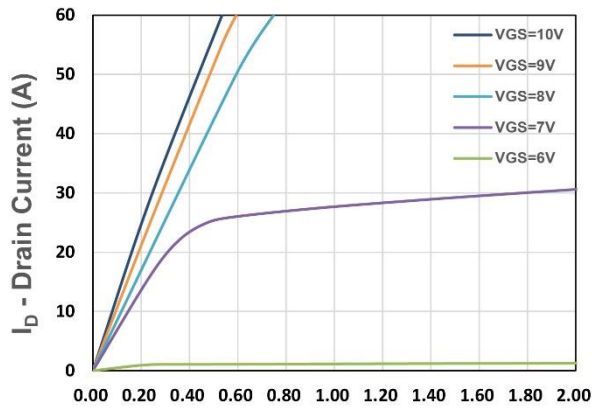
N-Channel Electrical Characteristics ($T_J=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250uA	150	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =120V, V _{GS} =0V	-	-	1	uA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250uA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ④	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A	-	8.5	10	mΩ
gfs	Forward Transconductance	V _{DS} =5V, I _{DS} =20A	-	76	-	S
Dynamic Characteristics ⑥						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V, Freq.=1MHz	-	1.1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =75V, Freq.=1MHz	-	4815	-	pF
C _{oss}	Output Capacitance		-	366	-	
C _{rss}	Reverse Transfer Capacitance		-	12.7	-	
td(ON)	Turn-on Delay Time	V _{GS} =10V,V _{DS} =75V, I _D =20A,R _{GEN} =10Ω	-	21	-	nS
t _r	Turn-on Rise Time		-	11	-	
t _{d(OFF)}	Turn-off Delay Time		-	32	-	
t _f	Turn-off Fall Time		-	13.2	-	
Q _g	Total Gate Charge	V _{GS} =10V,V _{DS} =75V, I _D =20A	-	57	-	nC
Q _{gs}	Gate-Source Charge		-	21	-	
Q _{gd}	Gate-Drain Charge		-	5.8	-	
Source-Drain Characteristics						
V _{SD} ④	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V	-	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, V _R =75V	-	88	-	nS
Q _{rr}	Reverse Recovery Charge	dI _F /dt=100A/μs	-	178	-	nC

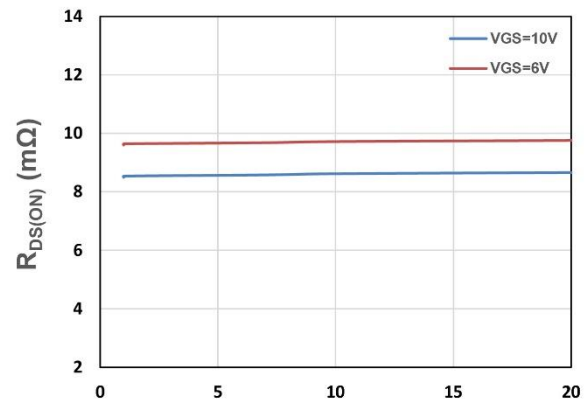
Note ④ : Pulse test (pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$).

Note ⑤ : Guaranteed by design, not subject to production testing.

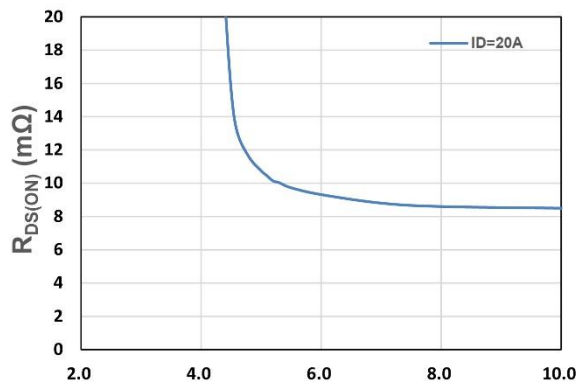
N-Channel Typical Characteristics



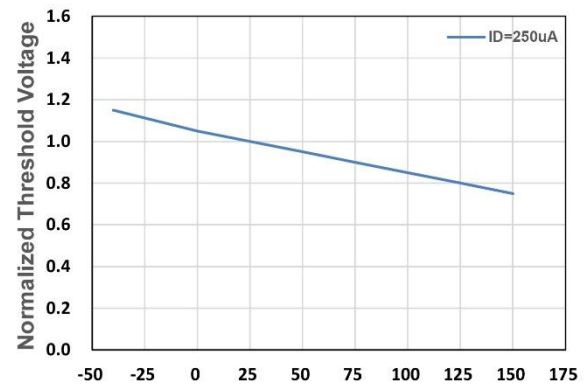
V_{DS} - Drain - Source Voltage (V)
Figure 1. Output Characteristics



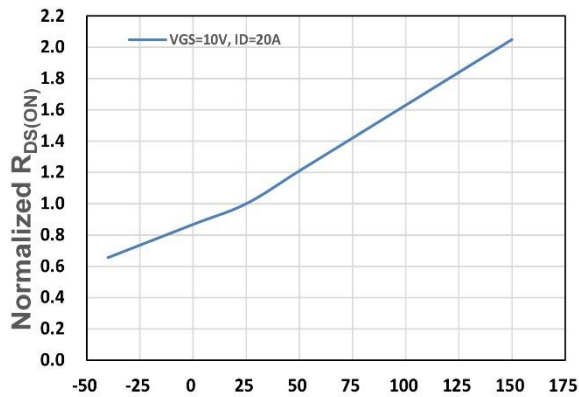
I_D - Drain Current (A)
Figure 2. On-Resistance vs. ID



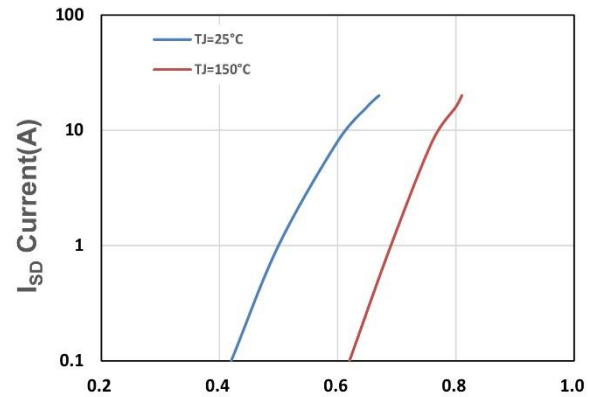
V_{GS} - Gate - Source Voltage (V)
Figure 3. On-Resistance vs. VGS



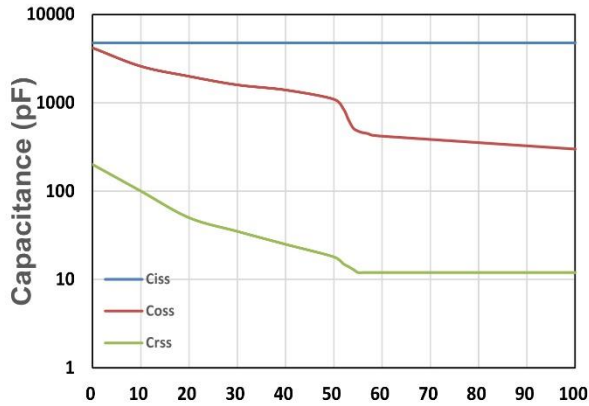
T_J , Junction Temperature(°C)
Figure 4. Gate Threshold Voltage



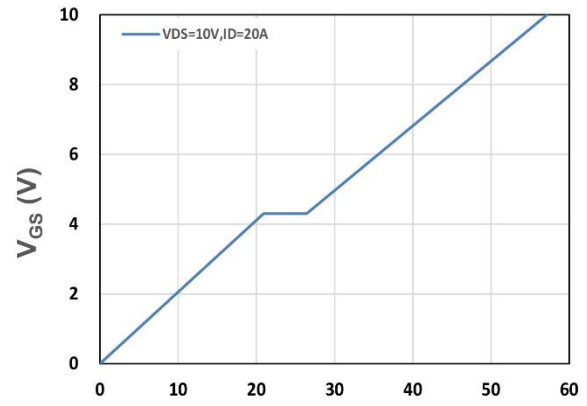
T_J , Junction Temperature(°C)
Figure 5. Drain-Source On Resistance



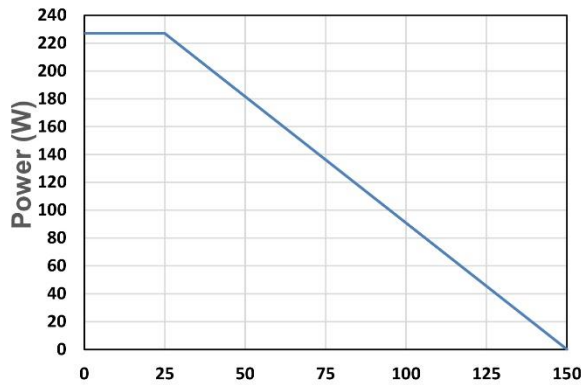
V_{SD} , Source-Drain Voltage(V)
Figure 6. Source-Drain Diode Forward



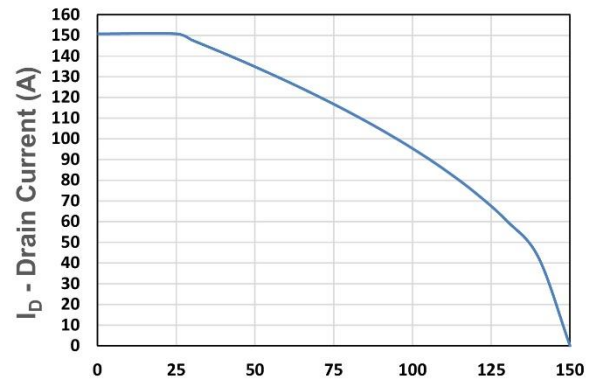
V_{DS} - Drain - Source Voltage (V)
Figure 7. Capacitance



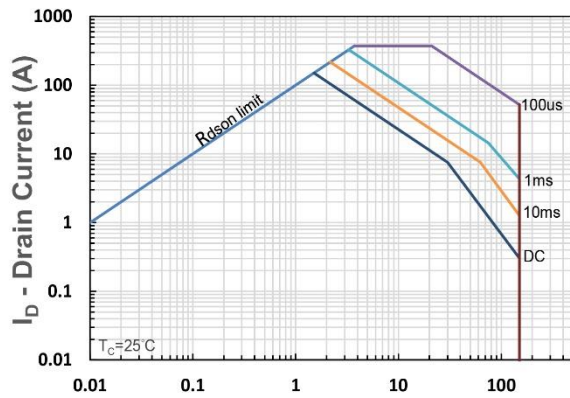
Q_g , Total Gate Charge (nC)
Figure 8. Gate Charge Characteristics



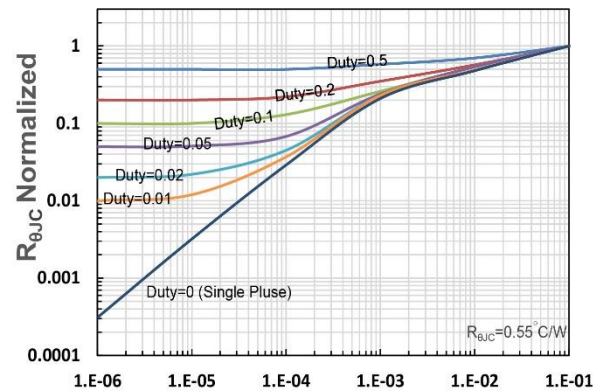
T_c - Case Temperature (°C)
Figure 9. Power Dissipation



T_c - Case Temperature (°C)
Figure 10. Drain Current



V_{DS} - Drain-Source Voltage (V)
Figure 11. Safe Operating Area



t_1 , Square Wave Pulse Duration(s)
Figure 12. $R_{\theta JC}$ Transient Thermal Impedance